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## ADVERTISEMENT



# Negative spin polarization at the Fermi level in Fe<sub>4</sub>N epitaxial films by spin-resolved photoelectron spectroscopy

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We evaluated the valence band structures of 10-nm-thick ferromagnetic Fe<sub>4</sub>N epitaxial films on SrTiO<sub>3</sub>(001) substrates at room temperature using spin-resolved photoelectron spectroscopy. Negative spin polarization is confirmed at the Fermi level. The experimentally obtained photoelectron spectra are well explained by first-principles calculations based on the psuedopotential method. © 2012 American Institute of Physics. [http://dx.doi.org/10.1063/1.4733327]

#### I. INTRODUCTION

Ferromagnetic Fe<sub>4</sub>N is a promising material for application in high performance spintronic devices. Fe<sub>4</sub>N has been extensively studied for magnetic recording media.<sup>1,2</sup> It has a cubic perovskite lattice structure, wherein a nitrogen atom is located in the body center of the fcc-Fe lattice. Spin polarization of the density of states (DOSs) (P) at the Fermi level  $(E_{\rm F})$  and spin asymmetry of the electrical conductivity  $(\beta)$ was calculated to be -0.6 and -1.0, respectively.<sup>3</sup> A recent theoretical calculation predicts that Co<sub>4</sub>N has a larger negative polarization than Fe<sub>4</sub>N.<sup>4</sup> In particular, a fully negative spin polarization (P = -1.0) at  $E_{\rm F}$  is predicted for Co<sub>3</sub>FeN.<sup>5</sup> We therefore expect that (Co,Fe)<sub>4</sub>N alloy is very promising for application in spintronics devices. We have previously measured the  $\beta$  values of Fe<sub>4</sub>N and pure Fe using point contact Andreev reflection (PCAR) and confirmed that Fe<sub>4</sub>N has a larger  $\beta$  than Fe.<sup>6</sup> We also measured spin and orbital magnetic moments of epitaxial Fe<sub>4</sub>N and Co<sub>4</sub>N films using x-ray magnetic circular dichroism.<sup>7,8</sup> An inverse tunnel magnetoresistance (TMR) ratio of -75% was reported in a CoFeB/MgO/Fe<sub>4</sub>N magnetic tunnel junction (MTJ),<sup>9</sup> and negative anisotropic magnetoresistance was observed in Fe<sub>4</sub>N films.<sup>10-12</sup> These results are thought to originate from the negative P and  $\beta$  in Fe<sub>4</sub>N.

The *P* value of material can be evaluated from a TMR ratio using Julliere's formula.<sup>13</sup> However, it is very sensitive to interface states at the ferromagnet/insulator interfaces in MTJ,<sup>14–16</sup> making it difficult to determine the *P* value. Also, the sign of  $\beta$  cannot be determined from a conductance curve in the PCAR measurement.<sup>17–19</sup> In contrast, spin-resolved photoelectron spectroscopy (SRPES) is an effective means to directly observe the spin-polarized DOS of ferromagnetic materials.<sup>20–23</sup> Dedkov *et al.* and Wang *et al.* showed that the values of *P* in half-metallic materials such as Fe<sub>3</sub>O<sub>4</sub> and Co<sub>2</sub>MnSi by SRPES.<sup>20,21</sup> The spin-resolved electrical struc-

tures at surfaces of Eu/Gd(0001) and YCo<sub>2</sub>/W(110) were also directly observed.<sup>22,23</sup> However, there have been no reports about SRPES measurements on Fe<sub>4</sub>N, (Co,Fe)<sub>4</sub>N, and Co<sub>4</sub>N films. In this study, we grew 10-nm-thick Fe<sub>4</sub>N films on SrTiO<sub>3</sub>(STO)(001) substrates by molecular beam epitaxy (MBE) and evaluated its spin dependent electronic structure near  $E_F$  using hard x-ray photoelectron spectroscopy (HX-PES) and SRPES.

#### **II. EXPERIMENTAL METHOD**

A  $CaF_2(1 nm)/Fe_4N(10 nm)$  layered structure was grown epitaxially by an ion-pumped MBE system. First, an Fe<sub>4</sub>N layer was formed on the STO(001) substrate by supplying 5N-Fe and radio frequency NH<sub>3</sub> plasma, simultaneously. Detailed growth procedures for Fe<sub>4</sub>N are described in our previous report.<sup>24</sup> After the growth of the Fe<sub>4</sub>N layer, a CaF<sub>2</sub> capping layer was formed at room temperature (RT), in order to prevent oxidation of the Fe<sub>4</sub>N layer. The CaF<sub>2</sub> capping layer has a large energy band gap of 12.1 eV (Ref. 25) and thereby does not influence photoelectron spectroscopy measurements. The crystalline quality of the Fe<sub>4</sub>N layer was characterized by reflection high-energy electron diffraction (RHEED) and  $\theta$ -2 $\theta$ x-ray diffraction (XRD). HX-PES measurements were performed at the undulator beamline BL15XU (Ref. 26) of SPring-8 in Japan. The valence band (VB) structures of Fe<sub>4</sub>N were measured by HX-PES with a photon energy of 5953 eV and overall energy resolution of 230 meV. The angle of incident light was 89° relative to the surface normal. We also calculated the spin-polarized DOS of Fe<sub>4</sub>N using the CASTEP (Ref. 27) code based on the density-functional theory in describing the electron-electron interaction, a pseudopotential description of the electron-core interaction, and a plane-wave expansion of the wavefunction, and compared them with experimentally obtained VB spectra. After the CaF<sub>2</sub> capping layer was removed by Ar ion sputtering (1-2 keV), and a clean Fe<sub>4</sub>N surface was obtained, spin-resolved VB structures near  $E_{\rm F}$  were measured by SRPES. The SRPES measurements

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were carried out at the Hiroshima Synchrotron Radiation Center.<sup>28</sup> Samples were excited by an unpolarized He I<sub> $\alpha$ </sub> resonance line ( $h\nu = 21.2 \text{ eV}$ ), and the overall energy resolution was 110 meV. The angle of incident light was 50° relative to the surface normal. Both HX-PES and SRPES measurements were performed at RT.

#### **III. RESULTS AND DISCUSSION**

Figure 1 shows the  $\theta$ -2 $\theta$  XRD pattern of the sample. The diffraction peaks of Fe<sub>4</sub>N (002) and (004) planes were observed. The inset shows the observed streaky RHEED pattern of the Fe<sub>4</sub>N layer along STO[110]. These results mean that the Fe<sub>4</sub>N layer was epitaxially grown on the STO substrate. From the XRD peak positions, we confirmed that the grown layers were almost strain-free Fe<sub>4</sub>N.

Figures 2(a) and 2(b) show the calculated partial DOSs of Fe 3*d*, Fe 4*s*, Fe 4*p*, N 2*s*, and N 2*p* states, and total DOSs of majority and minority spins in Fe<sub>4</sub>N, respectively. The VB structures mainly consist of the Fe 3*d* state, and the N state is dominant in the structures located at -7 and -17 eV. The negative spin polarization near  $E_{\rm F}$  is expected from Fig. 2(b). These features are in good agreement with the electrical VB structures derived by first-principle calculations.<sup>3,4,29–31</sup>

Figures 3(a) and 3(b) show the expected photoelectron spectra of Fe 3d and 4s states using the partial DOS of Fe<sub>4</sub>N multiplied by the photo-ionization cross-sections at a photon energy of 6 keV (Ref. 32) and the HX-PES VB photoelectron spectrum, respectively. In the wide HX-PES spectra, peak structures from Sr and Ti were observed (not shown), which indicates the substantially large probing depth. The contribution of N 2s and 2p states in the HX-PES spectrum should be negligibly small if their low photoionization cross sections are taken into account. We were not able to calculate the photoelectron spectrum of Fe 4p state because there have been no report so far on the photo-ionization cross-sections of Fe 4p state at a photon energy of 6 keV. We can see that the structures labeled A-F in Fig. 3(b) were well fitted to those labeled a-f in Fig. 3(a), although the overall structure differs slightly to each other. Structures B-E mainly consist of the Fe 3d state, and structures F and G are explained by the Fe 4s state. It is difficult to attribute the structure H,



FIG. 1.  $\theta$ -2 $\theta$  XRD and RHEED patterns of sample.

located at -12.5 eV in Fig. 3(b), to Fe<sub>4</sub>N. We think that this structure is related to other Fe-N phases in the Fe<sub>4</sub>N layers.

Figure 4 shows the Auger electron spectroscopy (AES) spectra, obtained using an incident electron energy of 3 keV, measured before and after removing the CaF<sub>2</sub> capping layer by Ar ion sputtering. The AES spectra were normalized by the signal intensity of Fe (LMM; 702 eV). Before the sputtering, intense signals corresponding to C (KLL; 269 eV) and O (KLL; 511 eV) were observed, in addition to those of Fe (LMM; 595, 648, and 702 eV), Ca (LMM; 292 eV), and F (KLL; 651 eV), as shown by the red curve. These C and O signals originate from contamination on the sample surface. After the sputtering (blue curve), the signals corresponding to Ca, F, C, and O disappeared and the signal for N (KLL; 384 eV) appeared instead. The Fe signal remained unchanged. These results confirmed the cleanliness of the sputtered sample surface of the Fe<sub>4</sub>N layer. SRPES measurements were subsequently performed without exposure to air.

Figure 5(a) shows the spin-resolved photoelectron spectra around  $E_{\rm F}$  measured by SRPES. The flat background signals due to secondary electrons caused by the He II resonance line ( $h\nu = 40.8 \,\mathrm{eV}$ ) were removed from raw spectra. Peak structures labeled A' and A" appear at  $-0.75 \,\mathrm{eV}$  in the majority spin state (red marks) and  $-0.45 \,\mathrm{eV}$  in the minority spin state (blue marks), respectively. These structures correspond to the structure A in Fig. 3(b), and agree with the calculated total DOS shown in Fig. 2(b). Figure 5(b) presents the spin polarization P near  $E_{\rm F}$  deduced from Fig. 5(a), that



FIG. 2. (a) Calculated partial DOSs for Fe 3d, Fe 4s, Fe 4p, N 2s, and N 2p states and (b) total DOSs of majority and minority spins in Fe<sub>4</sub>N.



FIG. 3. (a) Calculated photoemission spectra for Fe 3d and Fe 4s states in Fe<sub>4</sub>N. (b) HX-PES spectrum for Fe<sub>4</sub>N measured at photon energy of 5953 eV.

is, the majority spin states minus the minority spin states, divided by their sum. As shown in the figure, P value is approximately -0.2 at RT, being clearly negative at  $E_{\rm F}$ . We should note here that the P value is slightly shifted to the positive upward region in the wide range of energy due to the positive background signals. Therefore, it can be safely stated that Fe<sub>4</sub>N has a negative P at  $E_{\rm F}$ . In general, secondary electrons excited from ferromagnetic material have positive P because the number of excited electrons with majority spin is dominant in total. In our case, secondary electrons excited by He I<sub> $\alpha$ </sub> resonance line attribute to the background signals. In this work, we chose to adopt almost strain-free Fe<sub>4</sub>N epi-



FIG. 4. AES spectra of the sample (a) before (red curve) and (b) after (blue curve) removing the  $CaF_2$  capping layer by Ar ion sputtering.



FIG. 5. (a) SRPES spectra of majority (red marks) and minority (blue marks) spin states for  $Fe_4N$ . (b) Spin polarization of  $Fe_4N$  deduced from Fig. 5(a).

taxial layers for SRPES measurements. We do not have enough data to discuss the influence of crystalline quality of Fe<sub>4</sub>N on SRPES spectra. However, the SRPES spectra shown in Fig. 5(a) are attributed to the intrinsic properties of Fe<sub>4</sub>N. Thus, we speculate that the observed SRPES spectra themselves are not so much affected by the crystalline quality of Fe<sub>4</sub>N as far as the interatomic distances in Fe<sub>4</sub>N are not modified by something like strain and vacancies.

#### **IV. SUMMARY**

CaF<sub>2</sub>(1 nm)/Fe<sub>4</sub>N(10 nm)/STO(001) was grown by MBE, and the VB structures of Fe<sub>4</sub>N were characterized by photoelectron spectroscopy. Structures observed in the HX-PES spectra were explained by the calculated photoemission spectra of Fe 3*d* and 4*s* states in Fe<sub>4</sub>N. In the SRPES measurement, *P* was estimated having negative sign at  $E_F$  in spite of a positive shift due to secondary electrons.

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